

ABSTRACT

The present invention relates to a method for manufacturing a transflective thin film transistor liquid crystal display, which comprises the steps of: forming a gate electrode on an insulating substrate; forming a gate insulating film on the insulating substrate including the gate electrode; forming an active layer and an ohmic contact layer on the gate insulating film; forming source/drain electrodes on the insulating substrate including the active and ohmic contact layers in such a manner that the source/drain electrodes overlap with the ohmic contact layer; forming a protective film on the insulating substrate including the source/drain electrodes; forming a resin layer on the protective film; exposing the resin layer to light through one mask, so that a contact hole is formed at one region of the resin layer, and concave/convex portions having the desired concave/convex portions are formed on the other region of the resin layer; and forming a reflective electrode on the entire upper surface of the resulting substrate including the contact hole and the concave/convex portions.